SOD-323 Plastic-Encapsulate Diode

PRODUCT SUMMARY

RB551V-30 Schottky Diodes



FEATURES

High current rectifier Schottky diode
Low voltage, low inductance
For power supply

MARKING: D

Pb-free; RoHS-compliant

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Single Diode @ $T_A = 25^oC$

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	30	V
DC reverse voltage	V_R	20	V
Mean rectifying current	I_O	0.5	A
Peak forward surge current	I_{FSM}	2	A
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-40~+125	℃

ELECTRICAL RATINGS

@ $T_A = 25^oC$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F			0.36 0.47	V	I_F=100mA I_F=500mA
Reverse current	I_R			100	μA	V_R=20V

TYPICAL CHARACTERISTICS

Electrical Characteristic curves (T_a = 25°C)

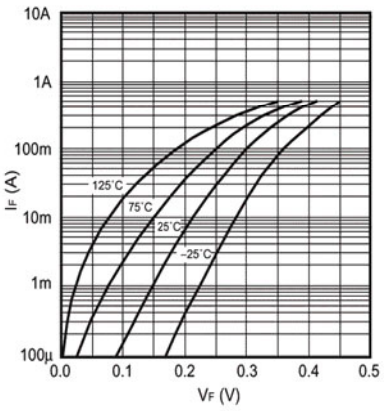


Fig.1 Forward characteristics

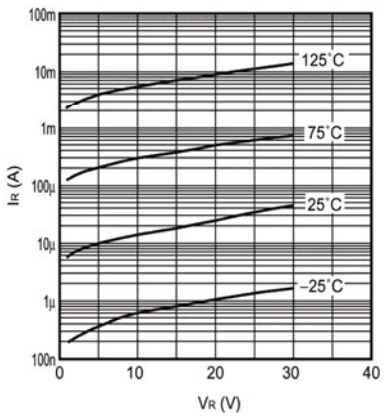


Fig.2 Reverse characteristics

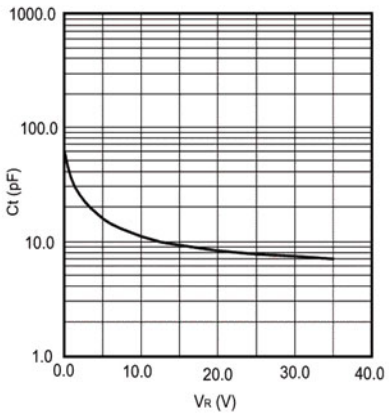


Fig.3 Capacitance between terminals characteristics

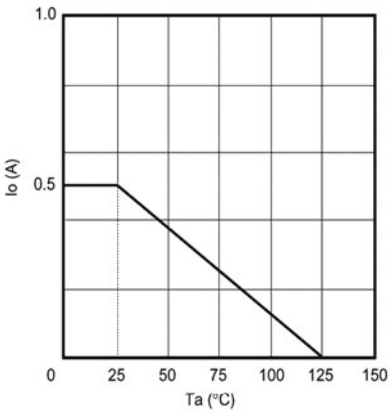


Fig.4 Derating curve

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